

### HIGH-SPEED 3.3V 8K x 16 DUAL-PORT STATIC RAM

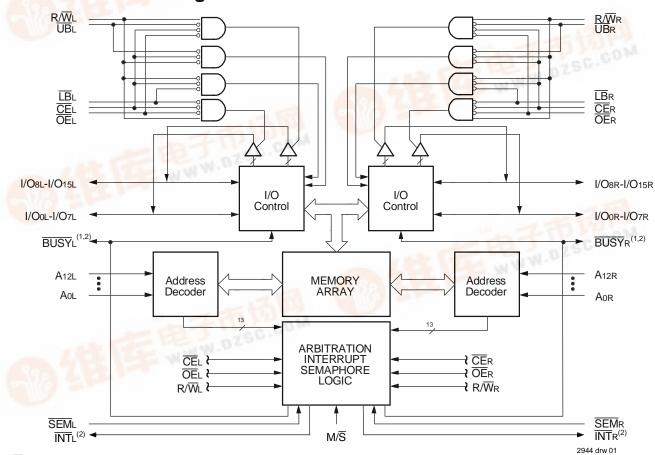
### IDT70V25S/L

### **Features**

- True Dual-Ported memory cells which allow simultaneous reads of the same memory location
- High-speed access
  - Commercial: 15/20/25/35/55ns (max.)
  - Industrial: 20/25/35/55ns (max.)
- Low-power operation
  - IDT70V25S
    - Active: 400mW (typ.) Standby: 3.3mW (typ.)
  - IDT70V25L
    - Active: 380mW (typ.) Standby: 660µW (typ.)
- Separate upper-byte and lower-byte control for multiplexed bus compatibility

- IDT70V25 easily expands data bus width to 32 bits or more using the Master/Slave select when cascading more than one device
- M/S = VIH for BUSY output flag on Master M/S = VIL for BUSY input on Slave
- BUSY and Interrupt Flag
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- LVTTL-compatible, single 3.3V (±0.3V) power supply
- Available in 84-pin PGA, 84-pin PLCC and 100-pin TQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds

### Functional Block Diagram



### **Description**

The IDT70V25 is a high-speed 8K x 16 Dual-Port Static RAM. The IDT70V25 is designed to be used as a stand-alone Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

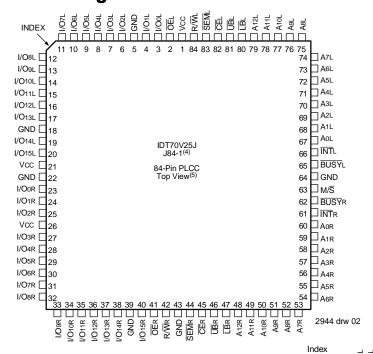
This device provides two independent ports with separate control,

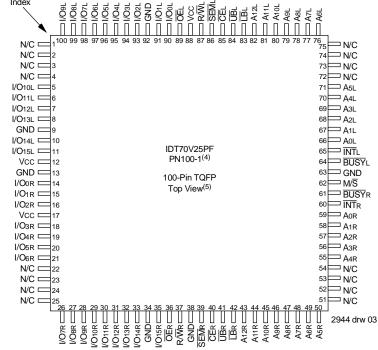
address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by  $\overline{\text{CE}}$  permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 400mW of power.

The IDT70V25 is packaged in a ceramic 84-pin PGA, an 84-Pin PLCC and a 100-pin Thin Quad Flatpack.

### Pin Configurations<sup>(1,2,3)</sup>





- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- J84-1 package body is approximately 1.15 in x 1.15 in x .17 in.
   PN100-1 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part marking.

## Pin Configurations<sup>(1,2,3)</sup> (con't.)

	63	61	60	58	55	54	51	48	46	45	42
11	I/O7L	I/O5L	I/O4L	I/O2L	I/OoL	ŌĒL	SEML	<u>∏</u> BL	A11L	A10L	A7L
	66	64	62	59	56	49	50	47	44	43	40
10	I/O10L	I/O8L	I/O6L	I/O3L	I/O1L	ŪB∟	CEL	A12L	A9L	A8L	A5L
	67	65			57	53	52		1	41	39
09	I/O11L	I/O9L			GND	Vcc	R/WL			A6L	A <sub>4</sub> L
	69	68	1			ı		J		38	37
80	I/O13L	I/O12L								AзL	A <sub>2</sub> L
	72	71	73						33	35	34
07	I/O15L	I/O14L	Vcc						BUSYL	AoL	ĪNT∟
	75	70	74		I	DT70V25 G84-3 <sup>(4)</sup>	iG		32	31	36
06	I/Oor	GND	GND		84-Pin PGA					M/S	A1L
	76	77	78			Top View	(5)		28	29	30
05	I/O1R	I/O2R	Vcc						Aor	ĪNTR	BUSYR
	79	80								26	27
04	I/O3R	I/O4R								A2R	A1R
	81	83	]		7	11	12			23	25
03	I/O5R	I/O7R			GND	GND	SEMR			A5R	A3R
	82	1	2	5	8	10	14	17	20	22	24
02	I/O6R	I/O9R	I/O10R	I/O13R	I/O15R	R/WR	<del>UB</del> R	A11R	A8R	A6R	A4R
	84	3	4	6	9	15	13	16	18	19	21
01	I/O8R	I/O11R	I/O12R	I/O14R	ŌĒR	LBR	CER	A12R	A10R	A9R	A7R
	A	В	С	D	Е	F	G	Н	J	К	L
Index											2944 drw 0

- All Vcc pins must be connected to power supply.
   All GND pins must be connected to ground supply.

- All GND pins must be connected to ground sappry.
   Package body is approximately 1.12 in x 1.12 in x 1.16 in.
   This package code is used to reference the package diagram.
   This text does not indicate orientation of the actual part marking.

### **Pin Names**

Left Port	Right Port	Names				
<u>CE</u> L	<del>CE</del> R	Chip Enable				
R/WL	R/W̄R	Read/Write Enable				
ŌĒL	<del>OE</del> R	Output Enable				
A0L - A12L	A0R - A12R	Address				
VO0L - I/O15L	VO0R - I/O15R	Data Input/Output				
SEML	SEMR	Semaphore Enable				
ŪB∟	ŪB̄R	Upper Byte Select				
ĪΒ̄ι	<del>LB</del> R	Lower Byte Select				
ĪNTL	ĪNTr	Interrupt Flag				
BUSYL	BUSYR	Busy Flag				
М	Ι <mark>S</mark>	Master or Slave Select				
V	CC	Power				
Gl	ND	Ground				

2944 tbl 01

### **Truth Table I: Non-Contention Read/Write Control**

		Inpu	ıts <sup>(1)</sup>			Out	puts		
ΖĒ	R/W	ŌĒ	ŪB	ĪΒ	SEM	I/O8-15	I/O <sub>0-7</sub>	Mode	
Н	Х	Χ	Χ	Х	Н	High-Z	High-Z	Deselected: Power Down	
Х	Х	Х	Н	Н	Н	High-Z	High-Z	Both Bytes Deselected	
L	L	Х	L	Н	Н	DATAIN	High-Z	Write to Upper Byte Only	
L	L	Х	Н	L	Н	High-Z	DATAIN	Write to Lower Byte Only	
L	L	Х	L	L	Н	DATAIN	DATAIN	Write to Both Bytes	
L	Н	L	L	Н	Н	DATAout	High-Z	Read Upper Byte Only	
L	Н	L	Н	L	Н	High-Z	<b>DATA</b> out	Read Lower Byte Only	
L	Н	L	L	L	Н	DATAout	DATAout	Read Both Bytes	
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled	

NOTE: 2944 tbl 02

1.  $A_{0L} - A_{12L} \neq A_{0R} - A_{12R}$ 

### Truth Table II: Semaphore Read/Write Control<sup>(1)</sup>

		Inp	uts			Out	puts	
CΕ	R/W	Œ	ŪB	IВ	SEM	I/O8-15	I/O <sub>0-7</sub>	Mode
Н	Н	L	Х	Х	L	DATAout	DATA оит	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	DATAout	DATA оит	Read Data in Semaphore Flag
Н	1	Х	Х	Х	L	DATAIN	DATAN	Write D№ into Semaphore Flag
Х	1	Х	Н	Н	L	DATAIN	DATAIN	Write D⊪o into Semaphore Flag
L	Х	Х	L	Х	L	_		Not Allowed
L	Х	Х	Х	L	L	_	_	Not Allowed

NOTE: 2944 tbl 03

<sup>1.</sup> There are eight semaphore flags written to via I/Oo and read from all of the I/O's (I/Oo-I/O15). These eight semaphores are addressed by Ao-A2.

### Absolute Maximum Ratings<sup>(1)</sup>

Symbol	Rating	Commercial & Industrial	Unit				
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +4.6	V				
TBIAS	Temperature Under Bias	-55 to +125	۰C				
Tstg	Storage Temperature	-55 to +125	°C				
ЮИТ	DC Output Current	50	mA				

2944 tbl 04

#### NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to  $\leq$  20mA for the period of VTERM  $\geq$  Vcc + 0.3V.

### **Capacitance**<sup>(1)</sup> (TA = +25°C, f = 1.0MHz)

Symbol	Parameter	Conditions <sup>(2)</sup>	Max.	Unit
Cin	Input Capacitance	V <sub>IN</sub> = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF

- 1. This parameter is determined by device characterization but is not production
- 2. 3dV references the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

### **Maximum Operating Temperature** and Supply Voltage (1)

Grade	Ambient Temperature	GND	Vcc		
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V		
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V		

1. This is the parameter Ta.

### **Recommended DC Operating Conditions**

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	V
GND	Ground	0	0	0	V
VIH	V⊪ Input High Voltage		_	Vcc+0.3 <sup>(2)</sup>	V
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>	_	0.8	V

2944 tbl 06

2944 tbl 05

#### NOTES:

- 1.  $V_{IL} \ge -1.5V$  for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 0.3V.

## **DC Electrical Characteristics Over the Operating** Temperature and Supply Voltage Range (Vcc = 3.3V ± 0.3V)

		<u> </u>					
			70V25S		70V		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
ILI	Input Leakage Current <sup>(1)</sup>	Vcc = 3.6V, $ViN = 0V$ to $Vcc$	_	10	-	5	μA
ILO	Output Leakage Current	$\overline{CE} = VIH$ , VOUT = 0V to VCC	-	10	ı	5	μA
Vol	Output Low Voltage	IOL = +4mA	_	0.4	-	0.4	V
Voh	Output High Voltage	IOH = -4mA	2.4	_	2.4	_	٧

1. At Vcc ≤ 2.0V input leakages are undefined.

2944 tbl 08

# DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup> ( $Vcc = 3.3V \pm 0.3V$ )

					70V25X15 Com'l Only		70V25X20 Com'l & Ind		70V25X25 Com'l & Ind		
Symbol	Parameter	Test Condition	Versio	on	Typ. <sup>(2)</sup>	Max.	Тур.(2)	Max.	Тур.(2)	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	$\overline{CE}$ = VII, Outputs Open $\overline{SEM}$ = VIH $f$ = $f_{MAX}^{(3)}$	COM'L	S L	150 140	215 185	140 130	200 175	130 125	190 165	mA
	(Buil Puis Active)	1 = IMAX**/	IND	S L	_		140 130	225 195	130 125	210 180	
<b> </b> SB1	Standby Current (Both Ports - TTL	CER and CEL = VIH SEMR = SEML = VIH f = MAX <sup>(3)</sup>	COM'L	S L	25 20	35 30	20 15	30 25	16 13	30 25	mA
	Level Inputs)		MIL & IND	S L			20 15	45 40	16 13	45 40	
ISB2	Standby Current (One Port - TTL	$\overline{CE}$ 'A" = VIL and $\overline{CE}$ 'B" = VIH <sup>(5)</sup> Active Port Outputs Open,	COM'L	S L	85 80	120 110	80 75	110 100	75 72	110 95	mA
	Level Inputs)	$\frac{f = f_{MAX}^{(3)}}{\overline{SEM}_{R}} = \overline{SEM}_{L} = V_{IH}$	MIL & IND	S L		-	80 75	130 115	75 72	125 110	
ISB3	Full Standby Current (Both Ports -	Both Ports $\overline{CE}L$ and $\overline{CER} \ge Vcc - 0.2V$ ,	COM'L	S L	1.0 0.2	5 2.5	1.0 0.2	5 2.5	1.0 0.2	5 2.5	mA
	CMOS Level Inputs) $ \begin{array}{l} \text{VIN} \geq \text{VCC} \cdot 0.2 \text{V or} \\ \text{VIN} \leq 0.2 \text{V, f} = 0^{(4)} \\ \hline \text{SEMR} = \overline{\text{SEML}} \geq \text{VCc-}0.2 \text{V} \\ \end{array} $		MIL & IND	S L			1.0 0.2	15 5	1.0 0.2	15 5	
ISB4	(One Port - $\overline{CE}^*B^* > VCC - 0.2V^{(5)}$		COM'L	S L	85 80	125 105	80 75	115 100	75 70	105 90	mA
	CMOS Level Inputs)		MIL & IND	S L	_		80 75	130 115	75 70	120 105	

2944 tbl 09a

					70V2 Coi & I	m'l	70V2 Co & I	m'l	
Symbol	Parameter	Test Condition	Version		Typ. <sup>(2)</sup>	Max.	Тур. <sup>(2)</sup>	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	$\overline{\overline{CE}} = \text{ViI, Outputs Open} \\ \overline{\overline{SEM}} = \text{ViH} \\ f = \text{Max}^{(3)}$	COM'L	S L	120 115	180 155	120 115	180 155	mA
	(Buil Polis Active)	1 = IMAX**/	IND	S L	120 115	200 170	120 115	200 170	
ISB1	Standby Current (Both Ports - TTL Level Inputs)		COM'L	S L	13 11	25 20	13 11	25 20	mA
	Level inputs)	1 = IMAX**	MIL & IND	S L	13 11	40 35	13 11	40 35	
ISB2	Standby Current (One Port - TTL	$\overline{\mathbb{C}}\mathbb{E}^{-A^*}=VIL$ and $\overline{\mathbb{C}}\mathbb{E}^{-B^*}=VIH^{(6)}$ Active Port Outputs Open, $f=f\text{Max}^{(3)}$	COM'L	S L	70 65	100 90	70 65	100 90	mA
	Level Inputs)	SEMR = SEML = VIH	MIL & IND	S L	70 65	120 105	70 65	120 105	
ISB3	Full Standby Current (Both Ports -	Both Ports ŒL and ŒR ≥ VCC - 0.2V,	COM'L	S L	1.0 0.2	5 2.5	1.0 0.2	5 2.5	mA
	ČMOS Level Inputs)	$V \mathbb{N} \ge V \mathbb{C} C - 0.2V$ or $V \mathbb{N} \le 0.2V$ , $f = 0^{(4)}$ $\overline{SEMR} = \overline{SEML} \ge V \mathbb{C} C - 0.2V$	MIL & IND	S L	1.0 0.2	15 5	1.0 0.2	15 5	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	$\overline{CE}^{A^*} \le 0.2V$ and $\overline{CE}^{B^*} \ge \underline{Vcc} \cdot 0.2V^{(5)}$ $\overline{SEMR} = \overline{SEML} \ge Vcc-0.2V$	COM'L	S L	65 60	100 85	65 60	100 85	mA
	Conos Level Inpuls)	SEINT = SEINT $\geq \sqrt{CC-0.2V}$ $\sqrt{N} \geq \sqrt{CC-0.2V}$ or $\sqrt{N} \leq 0.2V$ Active Port Outputs Open, $f = fmax^{(3)}$	MIL & IND	S L	65 60	115 100	65 60	115 100	

#### NOTES

- 1. 'X' in part number indicates power rating (S or L)
- 2. Vcc = 3.3V, TA = +25°C, and are not production tested. Icc dc = 115mA (typ.)
- 3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V
- 4. f = 0 means no address or control lines change.
- 5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2944 tbl 09b

### **AC Test Conditions**

AO ICST Obligitions	
Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2
	2944 tbl 10

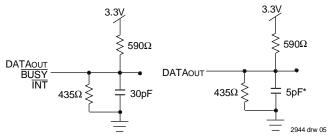
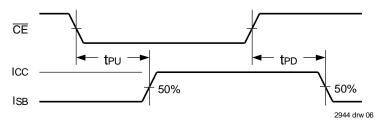


Figure 1. AC Output Test Load

Figure 2. Output Test Load (For tLz, tHz, twz, tow) \*Including scope and jig.

### **Timing of Power-Up Power-Down**



### **AC Electrical Characteristics Over the** Operating Temperature and Supply Voltage Range<sup>(4)</sup>

	Parameter		70V25X15 Com'l Only		70V25X20 Com'l & Ind		70V25X25 Com'l & Ind	
Symbol			Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	15	_	20		25	_	ns
taa	Address Access Time		15	-	20		25	ns
tace	Chip Enable Access Time <sup>(3)</sup>	_	15	_	20	_	25	ns
tabe	Byte Enable Access Time <sup>(3)</sup>	_	15	_	20	_	25	ns
taoe	Output Enable Access Time <sup>(3)</sup>	_	10	_	12		13	ns
tон	Output Hold from Address Change	3	_	3	_	3	_	ns
tLZ	Output Low-Z Time <sup>(1,2)</sup>	3	_	3	_	3	_	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	10	_	12	_	15	ns
tpu	Chip Enable to Power Up Time <sup>(1,2)</sup>	0	_	0	_	0		ns
tPD	Chip Disable to Power Down Time <sup>(1,2)</sup>		15	_	20		25	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10		10		10		ns
tsaa	Semaphore Address Access <sup>(3)</sup>		15	_	20		25	ns

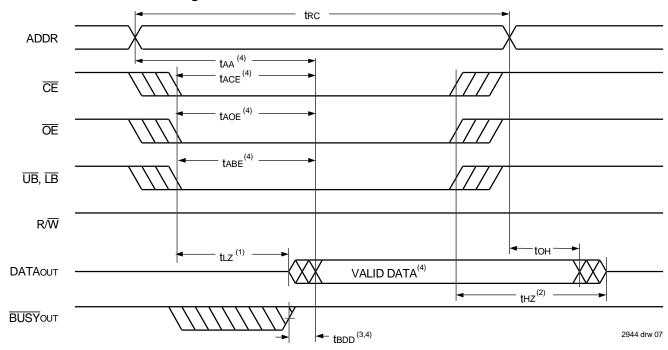
2944 tbl 11a

2944 tbl 11b

			5X35 m'l Ind	70V2 Co &		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
trc	Read Cycle Time	35	_	55	_	ns
taa	Address Access Time	_	35	_	55	ns
tace	Chip Enable Access Time <sup>(3)</sup>	_	35		55	ns
<b>t</b> ABE	Byte Enable Access Time <sup>(3)</sup>	_	35		55	ns
taoe	Output Enable Access Time <sup>(3)</sup>	-	20		30	ns
tон	Output Hold from Address Change	3	_	3	_	ns
t_z	Output Low-Z Time <sup>(1,2)</sup>	3	_	3	_	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	15	_	25	ns
tpu	Chip Enable to Power Up Time (1,2)	0	_	0	_	ns
tPD	Chip Disable to Power Down Time <sup>(1,2)</sup>	_	35	_	50	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	15	_	15		ns
tsaa	Semaphore Address Access <sup>(3)</sup>	_	35		55	ns

- 1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- This parameter is guaranteed by device characterization, but is not production tested.
   To access RAM, CE = VIL, UB or LB = VIL, and SEM = VIL. To access semaphore, CE = VIH or UB & LB = VIH, and SEM = VIL.
- 4. 'X' in part number indicates power rating (S or L).

### Waveform of Read Cycles<sup>(5)</sup>



- Timing depends on which signal is asserted last, OE, CE, LB, or UB.
   Timing depends on which signal is de-asserted first, CE, OE, LB, or UB.
- 3. tbbb delay is required only in case where opposite port is completing a write operation to the same address location for simultaneous read operations BUSY has no
- 4. Start of valid data depends on which timing becomes effective last tabe, tace, ta
- 5.  $\overline{SEM} = VIH.$

# AC Electrical Characteristics Over the Operating Temperature and Supply Voltage (5)

	0 1 11 3										
		70V25X15 Com'l Only		70V25X20 Com'l & Ind		70V25X25 Com'l & Ind					
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit			
WRITE CYCLI	WRITE CYCLE										
twc	Write Cycle Time	15	_	20	_	25	_	ns			
tew	Chip Enable to End-of-Write <sup>(3)</sup>	12	_	15	_	20	_	ns			
taw	Address Valid to End-of-Write	12	_	15	_	20	_	ns			
tas	Address Set-up Time <sup>(3)</sup>	0	_	0	_	0	_	ns			
twp	Write Pulse Width	12	_	15	_	20	_	ns			
twr	Write Recovery Time	0	_	0	_	0	_	ns			
tow	Data Valid to End-of-Write	10	_	15	_	15	_	ns			
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	10	_	12	_	15	ns			
toн	Data Hold Time <sup>(4)</sup>	0	_	0	_	0	_	ns			
twz	Write Enable to Output in High-Z <sup>(1,2)</sup>	_	10	_	12	_	15	ns			
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0	_	0	_	0	_	ns			
tswrd	SEM Flag Write to Read Time	5	_	5	_	5	_	ns			
tsps	SEM Flag Contention Window	5	_	5	_	5	_	ns			

2944 tbl 12a

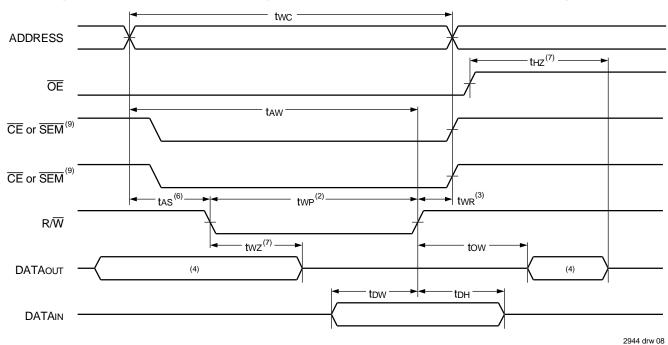
		Co	5X35 m'l Ind	70V25X55 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCLE	<u> </u>					
twc	Write Cycle Time	35	_	55	_	ns
tew	Chip Enable to End-of-Write <sup>(3)</sup>	30	_	45	_	ns
taw	Address Valid to End-of-Write	30	_	45	_	ns
tas	Address Set-up Time <sup>(3)</sup>	0	_	0	-	ns
twp	Write Pulse Width	25	_	40	-	ns
twr	Write Recovery Time	0	_	0	1	ns
tow	Data Valid to End-of-Write	15	_	30	ı	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	15	_	25	ns
tон	Data Hold Time <sup>(4)</sup>	0	_	0	-	ns
twz	Write Enable to Output in High-Z <sup>(1,2)</sup>	_	15	_	25	ns
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0	_	0	-	ns
tswrd	SEM Flag Write to Read Time	5	_	5	-	ns
tsps	SEM Flag Contention Window	5	_	5	_	ns

#### NOTES:

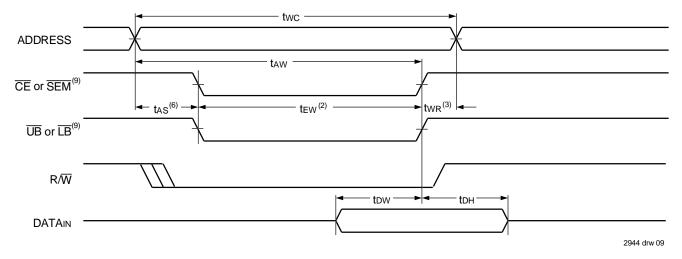
2944 tbl 12b

- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. To access SRAM,  $\overline{CE} = V_{IL}$ ,  $\overline{UB}$  or  $\overline{LB} = V_{IL}$ ,  $\overline{SEM} = V_{IH}$ . To access semaphore,  $\overline{CE} = V_{IH}$  or  $\overline{UB}$  &  $\overline{LB} = V_{IH}$ , and  $\overline{SEM} = V_{IL}$ . Either condition must be valid for the entire tew time.
- 4. The specification for IDH must be met by the device supplying write data to the SRAM under all operating conditions. Although IDH and tow values will vary over voltage and temperature, the actual IDH will always be smaller than the actual tow.
- 5. 'X' in part number indicates power rating (S or L).

## Timing Waveform of Write Cycle No. 1, R/W Controlled Timing<sup>(1,5,8)</sup>

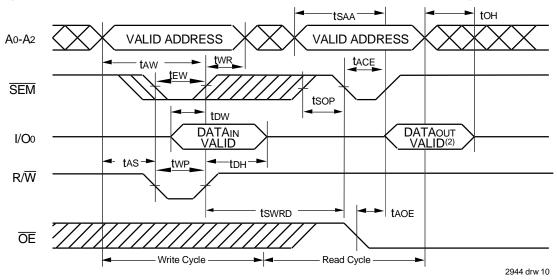


### Timing Waveform of Write Cycle No. 2, CE, UB, LB Controlled Timing<sup>(1,5)</sup>



- 1. R/W or CE or UB & LB must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or two) of a LOW  $\overline{\text{UB}}$  or  $\overline{\text{LB}}$  and a LOW  $\overline{\text{CE}}$  and a LOW  $\overline{\text{RW}}$  for memory array writing cycle.
- 3. twn is measured from the earlier of  $\overline{\text{CE}}$  or  $\overline{\text{R/W}}$  (or  $\overline{\text{SEM}}$  or  $\overline{\text{R/W}}$ ) going HIGH to the end-of-write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the  $\overline{\text{CE}}$  or  $\overline{\text{SEM}}$  LOW transition occurs simultaneously with or after the  $\overline{\text{R/W}}$  LOW transition the outputs remain in the HIGH-impedance state.
- 6. Timing depends on which enable signal is asserted last,  $\overline{CE}$ ,  $R/\overline{W}$ , or  $\overline{UB}$  or  $\overline{LB}$ .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with Output Test Load (Figure 2).
- 8. If  $\overline{OE}$  is LOW during R $\overline{W}$  controlled write cycle, the write pulse width must be the larger of twp or (twz + tbw) to allow the I/O drivers to turn off and data to be placed on the bus for the required tbw. If  $\overline{OE}$  is HIGH during an R $\overline{W}$  controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access SRAM,  $\overline{CE} = VIL$ ,  $\overline{UB}$  or  $\overline{LB} = VIL$ , and  $\overline{SEM} = VIH$ . To access Semaphore,  $\overline{CE} = VIH$  or  $\overline{UB}$  and  $\overline{LB} = VIH$ , and  $\overline{SEM} = VIL$  tew must be met for either condition.

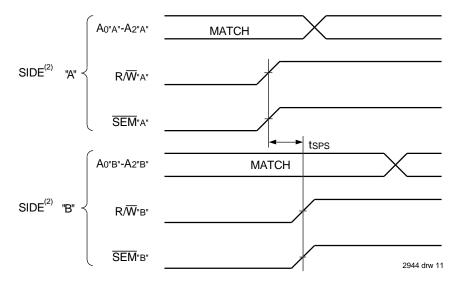
### Timing Waveform of Semaphore Read after Write Timing, Either Side<sup>(1)</sup>



#### NOTES

- 1.  $\overline{\text{CE}}$  = ViH or  $\overline{\text{UB}}$  &  $\overline{\text{LB}}$  = ViH for the duration of the above timing (both write and read cycle).
- 2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

### Timing Waveform of Semaphore Write Contention (1,3,4)



- 1.  $DOR = DOL = VIL, \overline{CE}R = \overline{CE}L = VIH, or both \overline{UB} \& \overline{LB} = VIH.$
- 2. All timing is the same for left and right port. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from  $R/\overline{W}^*A^*$  or  $\overline{SEM}^*A^*$  going HIGH to  $R/\overline{W}^*B^*$  or  $\overline{SEM}^*B^*$  going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will obtain the semaphore flag.

### **AC Electrical Characteristics Over the** Operating Temperature and Supply Voltage Range<sup>(6)</sup>

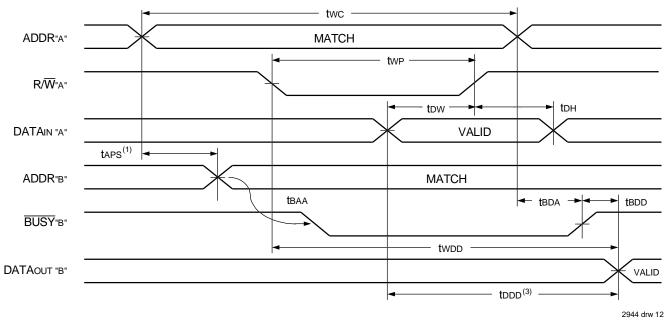
		70V25X15 Com'l Ony		70V25X20 Com'l & Ind		70V25X25 Com'l & Ind				
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit		
BUSY TIMING (M/S = Vih)										
tbaa	BUSY Access Time from Address Match	_	15		20	_	20	ns		
tBDA	BUSY Disable Time from Address Not Matched	_	15		20		20	ns		
tBAC	BUSY Access Time from Chip Enable LOW	_	15	_	20	_	20	ns		
tBDC	BUSY Disable Time from Chip Enable HIGH	_	15	_	17	_	17	ns		
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5	_	5	_	5	_	ns		
tBDD	BUSY Disable to Valid Data <sup>(3)</sup>	_	18	_	30	_	30	ns		
twн	Write Hold After BUSY <sup>(5)</sup>	12	-	15	_	17	_	ns		
<b>BUSY</b> TIMING	$(M/\overline{S} = V_{IL})$									
twB	BUSY Input to Write <sup>(4)</sup>	0		0		0	_	ns		
twн	Write Hold After BUSY <sup>(5)</sup>	12		15		17	_	ns		
PORT-TO-POR	RT DELAY TIMING									
twdd	Write Pulse to Data Delay <sup>(1)</sup>	_	30		45	_	50	ns		
todo	Write Data Valid to Read Data Delay(1)	_	25	_	35	_	35	ns		

2944 tbl 13a

		70V25X35 Com'l & Ind		70V25X55 Com'l & Ind						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
BUSY TIMING (M/S = Vih)										
tbaa	BUSY Access Time from Address Match		20	-	45	ns				
tBDA	BUSY Disable Time from Address Not Matched		20		40	ns				
t <sub>BAC</sub>	BUSY Access Time from Chip Enable LOW	_	20	_	40	ns				
tBDC	BUSY Disable Time from Chip Enable HIGH	_	20	_	35	ns				
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5	_	5	_	ns				
tBDD	BUSY Disable to Valid Data <sup>(5)</sup>	_	35	_	40	ns				
twн	Write Hold After BUSY <sup>(5)</sup>	25	_	25	_	ns				
<b>BUSY</b> TIMING	$(M/\overline{S} = V_{IL})$									
twB	BUSY Input to Write <sup>(4)</sup>	0	1	0	1	ns				
twн	Write Hold After BUSY <sup>(5)</sup>	25	_	25		ns				
PORT-TO-POR	PORT-TO-PORT DELAY TIMING									
twdd	Write Pulse to Data Delay <sup>(1)</sup>	_	60	_	80	ns				
todo	Write Data Valid to Read Data Delay <sup>(1)</sup>	_	45	_	65	ns				

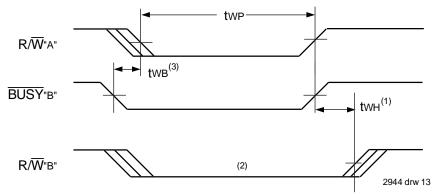
- 1. Port-to-port delay through SRAM cells from writing port to reading port, refer to "TIMING WAVEFORM OF WRITE PORT-TO-PORT READ AND  $\overline{BUSY}$  (M/ $\overline{S} = VIH$ )".
- 2. To ensure that the earlier of the two ports wins.
- 3. tbdd is a calculated parameter and is the greater of 0, twdd twp (actual) or tddd tdw (actual).
- 4. To ensure that the write cycle is inhibited during contention.
- 5. To ensure that a write cycle is completed after contention.
- 6. 'X' in part number indicates power rating (S or L).

# Timing Waveform of Write Port-to-Port Read and $\overline{BUSY}^{(2,4,5)}$ (M/ $\overline{S}$ = VIH)



- 1. To ensure that the earlier of the two ports wins. taps is ignored for  $M/\overline{S} = VIL$  (slave).
- 2.  $\overline{CE}L = \overline{CE}R = VIL$
- 3.  $\overline{OE}$  = VIL for the reading port.
- If M/S = VIL (slave), BUSY is an input. Then for this example BUSY\*A" = VIH and BUSY\*B" input is shown above.
   All timing is the same for both left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

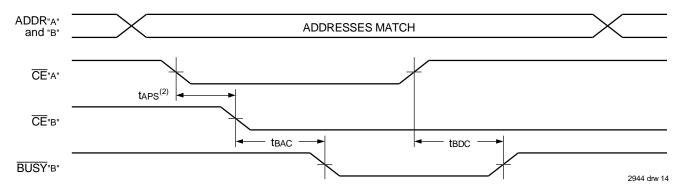
## Timing Waveform of Write with BUSY



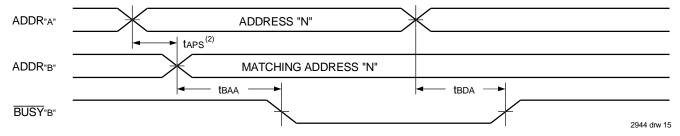
#### NOTES

- 1. twh must be met for both master BUSY input (slave) and output (master).
- 2. BUSY is asserted on port "B" blocking R/W B", until BUSY B goes HIGH.
- 3. twb is only for the slave version.

### Waveform of $\overline{BUSY}$ Arbitration Controlled by $\overline{CE}$ Timing<sup>(1)</sup> (M/ $\overline{S}$ = VIH)



# Waveform of $\overline{BUSY}$ Arbitration Cycle Controlled by Address Match Timing<sup>(1)</sup> (M/ $\overline{S}$ = VIH)



- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
- 2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1)</sup>

	<u> </u>							
			70V25X15 Com'l Only		70V25X20 Com'l & Ind		70V25X25 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
INTERRUPT T	IMING							
tas	Address Set-up Time	0	_	0	_	0	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tins	Interrupt Set Time		15	_	20	_	20	ns
tinr	Interrupt Reset Time	_	15	_	20	_	20	ns

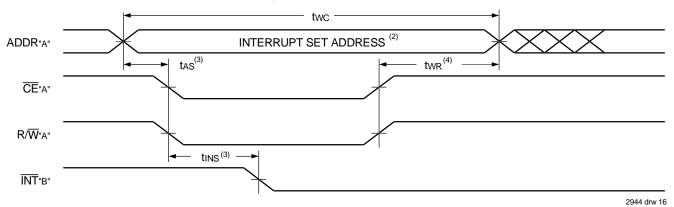
2944 tbl 14a

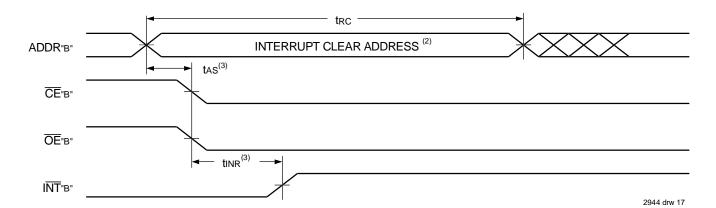
		Co	5X35 m'l Ind	70V25X55 Com'l & Ind						
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit				
INTERRUPT T	NTERRUPT TIMING									
tas	Address Set-up Time	0	_	0	_	ns				
twr	Write Recovery Time	0	_	0	_	ns				
tins	Interrupt Set Time	1	25	_	40	ns				
tinr	Interrupt Reset Time	1	25		40	ns				

### NOTES:

1. 'X' in part number indicates power rating (S or L).

# Waveform of Interrupt Timing<sup>(1)</sup>





- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
- 2. See Interrupt Flag Truth Table III.
- Timing depends on which enable signal (CE or R/W) is asserted last.
   Timing depends on which enable signal (CE or R/W) is de-asserted first.

Truth Table III — Interrupt Flag<sup>(1)</sup>

					<u> </u>								
		Right Port						Left Port					
Function	Ī <b>NT</b> R	A12R-A0R	<b>ŌĒ</b> R	<b>C</b> ĒR	R/W̄R	ĪNTL	A12L-A0L	ŌĒL	<u>C</u> Ē∟	R/W L			
Set Right INTR Flag	L(2)	Х	Х	Х	Х	Х	1FFF	Х	L	L			
Reset Right INTR Flag	H <sup>(3)</sup>	1FFF	L	L	Х	Х	Х	Х	Х	Х			
Set Left INTL Flag	Х	1FFE	Х	L	L	L <sup>(3)</sup>	Х	Х	Х	Х			
Reset Left INTL Flag	Х	Х	Х	Х	Х	H <sup>(2)</sup>	1FFE	L	L	Х			

#### NOTES:

- 1. Assumes  $\overline{BUSY}_L = \overline{BUSY}_R = VIH$ .
- 2. If  $\overline{BUSY}L = VIL$ , then no change.
- 3. If  $\overline{BUSY}R = VIL$ , then no change.

### **Truth Table IV — Address BUSY Arbitration**

	ln	puts	Out	puts	
CEL	<del>C</del> ER	A12L-A0L A12R-A0R	BUSY <sub>L</sub> (1)	BUSY <sub>R</sub> (1)	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Χ	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

2944 tbl 16

- 1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70V25 are push pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.
- 2. L if the inputs to the opposite port were stable prior to the address and enable inputs of this port. VIH if the inputs to the opposite port became stable after the address and enable inputs of this port. If taps is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs cannot be LOW simultaneously.
- 3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

### Truth Table V — Example of Semaphore Procurement Sequence (1,2,3)

Functions	Do - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

#### NOTES:

- 1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V25.
- There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O15). These eight semaphores are addressed by Ao-A2.
- 3.  $\overline{CE} = V_{IH}$ ,  $\overline{SEM} = V_{IL}$  to access the semaphores. Refer to the Semaphore Read/Write Control Truth Tables.

2944 thl 17

2944 tbl 15

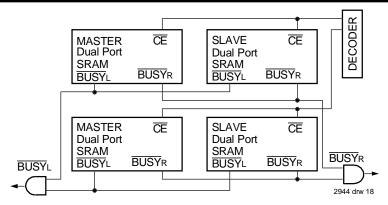


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V25 SRAMs.

### **Functional Description**

The IDT70V25 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V25 has an automatic power down feature controlled by  $\overline{\text{CE}}$ . The  $\overline{\text{CE}}$  controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{\text{CE}}$  HIGH). When a port is enabled, access to the entire memory array is permitted.

### **Interrupts**

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag ( $\overline{\text{INT}}\text{L}$ ) is asserted when the right port writes to memory location 1FFE (HEX), where a write is defined as the  $\overline{\text{CE}}\text{R} = R/\overline{\text{W}}\text{R} = \text{V}_{\text{IL}}$  per Truth Table III. The left port clears the interrupt by an address location 1FFE access when  $\overline{\text{CE}}\text{L} = \overline{\text{OE}}\text{L} = \text{V}_{\text{IL}}$ ,  $R/\overline{\text{WL}}$  is a "don't care". Likewise, the right port interrupt flag ( $\overline{\text{INT}}\text{R}$ ) is set when the left port writes to memory location 1FFF (HEX) and to clear the interrupt flag ( $\overline{\text{INT}}\text{R}$ ), the right port must read the memory location 1FFF. The message (16 bits) at 1FFE or 1FFF is user-defined, since it is an addressable SRAM location. If the interrupt function is not used, address locations 1FFE and 1FFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table III for the interrupt operation.

### **Busy Logic**

Busy Logic provides a hardware indication that both ports of the SRAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the SRAM is "busy". The  $\overline{\text{BUSY}}$  pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a  $\overline{\text{BUSY}}$  indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{\text{BUSY}}$  outputs together and use any  $\overline{\text{BUSY}}$  indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of  $\overline{\text{BUSY}}$  logic is not desirable, the  $\overline{\text{BUSY}}$  logic can be disabled by placing the part in slave mode with the  $\overline{\text{M/S}}$  pin. Once in slave mode the  $\overline{\text{BUSY}}$  pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the  $\overline{\text{BUSY}}$  pins HIGH. If desired, unintended

write operations can be prevented to a port by tying the  $\overline{\text{BUSY}}$  pin for that port LOW.

The BUSY outputs on the IDT 70V25 SRAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these SRAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

# Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V25 SRAM array in width while using  $\overline{\text{BUSY}}$  logic, one master part is used to decide which side of the SRAM array will receive a  $\overline{\text{BUSY}}$  indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the  $\overline{\text{BUSY}}$  signal as a write inhibit signal. Thus on the IDT70V25 SRAM the  $\overline{\text{BUSY}}$  pin is an output if the part is used as a master (M/ $\overline{\text{S}}$  pin = VIH), and the  $\overline{\text{BUSY}}$  pin is an input if the part used as a slave (M/ $\overline{\text{S}}$  pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating  $\overline{BUSY}$  on one side of the array and another master indicating  $\overline{BUSY}$  on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The  $\overline{BUSY}$  arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a  $\overline{BUSY}$  flag to be output from the master before the actual write pulse can be initiated with either the  $R/\overline{W}$  signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

### **Semaphores**

The IDT70V25 is an extremely fast Dual-Port 8K x 16 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port SRAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port SRAM or any other

shared resource.

The Dual-Port SRAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be accessed at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port SRAM. These devices have an automatic power-down feature controlled by CE, the Dual-Port SRAM enable, and SEM, the semaphore enable. The CE and SEM pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table I where  $\overline{\text{CE}}$  and  $\overline{\text{SEM}}$  are both HIGH.

Systems which can best use the IDT70V25 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V25's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V25 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

### **How the Semaphore Flags Work**

The semaphore logic is a set of eight latches which are independent of the Dual-Port SRAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70V25 in a separate memory space from the Dual-Port SRAM. This address space is accessed by placing a LOW input on the SEM pin (which acts

as a chip select for the semaphore flags) and using the other control pins (Address,  $\overline{OE}$ , and  $R/\overline{W}$ ) as they would be used in accessing a standard static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a LOW level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table V). That semaphore can now only be modi-fied by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select ( $\overline{SEM}$ ) and output enable ( $\overline{OE}$ ) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal ( $\overline{SEM}$  or  $\overline{OE}$ ) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Truth Table V). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The

second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

### **Using Semaphores—Some Examples**

Perhaps the simplest application of semaphores is their application as resource markers for the IDT70V25's Dual-Port SRAM. Say the 8K x 16 SRAM was to be divided into two 4K x 16 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 4K of Dual-Port SRAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 4K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain

control of the second 4K section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 4K blocks of Dual-Port SRAM with each other.

The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port SRAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.

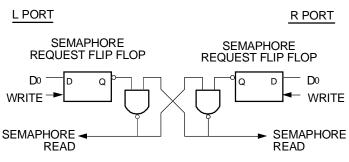
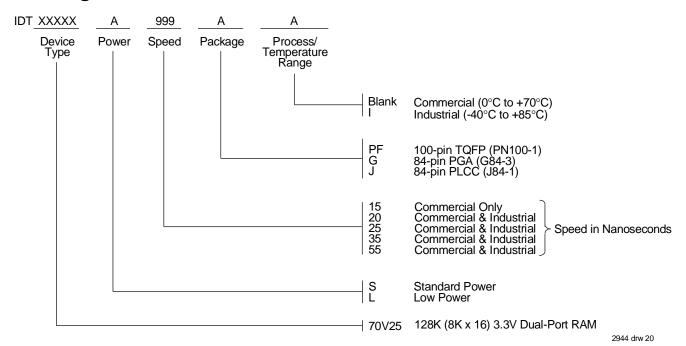


Figure 4. IDT70V25 Semaphore Logic

2944 drw 19

### Ordering Information(1)



### **Datasheet Document History**

3/8/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections

Pages 2 and 3 Added additional notes to pin configurations

5/19/99: Page 9 Fixed typographical error 6/10/99: Changed drawing format

8/30/99: Page 1 Chaged 660mW to 660μW

11/12/99: Replaced IDT logo

11/18/99: Page 2 Fixed pin 55 in PN100 package

3/10/00: Added 15 & 20ns speed grades

Upgraded DC parameters

Added Industrial Temperature information Changed ±200 mV to 0mV in notes

5/16/00: Page 5 Fixed note for Absolute Maximum Ratings table



CORPORATE HEADQUARTERS

2975 Stender Way Santa Clara, CA 95054 for SALES:

800-345-7015 or 408-727-6116

fax: 408-492-8674

www.idt.com

831-754-4613 DualPortHelp@idt.com

for Tech Support: